

NTR3A30PZ

MOSFET – Power, Single P-Channel, SOT-23, 2.4 x 2.9 x 1.0 mm

-20 V, -5.5 A

Features

- Low $R_{DS(on)}$ Solution in 2.4 mm x 2.9 mm Package
- ESD Diode-Protected Gate
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- High Side Load Switch
- Battery Switch
- Optimized for Power Management Applications for Portable Products, such as Smart Phones, Media Tablets, PMP, DSC, GPS, and Others

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

| Parameter | | Symbol | Value | Unit | |
|---|------------------------|--------------------------|--------------------------|----------------------|---|
| Drain-to-Source Voltage | | V_{DSS} | -20 | V | |
| Gate-to-Source Voltage | | V_{GS} | ± 8 | V | |
| Drain Current (Note 1) Drain Current (Note 1) | Steady State | I_D | $T_A = 25^\circ\text{C}$ | -3.0 | A |
| | | | $T_A = 85^\circ\text{C}$ | -2.2 | |
| | $t \leq 5 \text{ s}$ | $T_A = 25^\circ\text{C}$ | -5.5 | | |
| Power Dissipation (Note 1) | Steady State | P_D | $T_A = 25^\circ\text{C}$ | | W |
| | | | | $t \leq 5 \text{ s}$ | |
| Pulsed Drain Current | $t_p = 10 \mu\text{s}$ | I_{DM} | -9.1 | A | |
| Operating Junction and Storage Temperature | | T_J, T_{STG} | -55 to 150 | $^\circ\text{C}$ | |
| ESD HBM, JESD22-A114 | | V_{ESD} | 2000 | V | |
| Source Current (Body Diode) (Note 2) | | I_S | -0.48 | A | |
| Lead Temperature for Soldering Purposes (1/8 in from case for 10 s) | | T_L | 260 | $^\circ\text{C}$ | |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Max | Unit |
|---|-----------------|-----|--------------------|
| Junction-to-Ambient – Steady State (Note 1) | $R_{\theta JA}$ | 260 | $^\circ\text{C/W}$ |
| Junction-to-Ambient – $t \leq 5 \text{ s}$ (Note 1) | $R_{\theta JA}$ | 79 | |

1. Surface-mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq. [2 oz] including traces).
2. Pulse Test: pulse width $\leq 300 \text{ ms}$, duty cycle $\leq 2\%$.

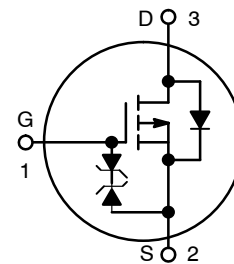


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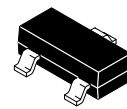
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| $V_{(BR)DSS}$ | $R_{DS(on)}$ Max | I_D MAX |
|---------------|------------------------|-----------|
| -20 V | 38 m Ω @ -4.5 V | -5.5 A |
| | 50 m Ω @ -2.5 V | |
| | 73 m Ω @ -1.8 V | |

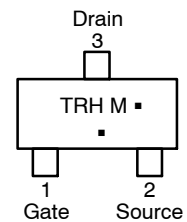
P-Channel MOSFET



MARKING DIAGRAM & PIN ASSIGNMENT



**SOT-23
CASE 318
STYLE 21**



TRH = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping† |
|--------------|------------------|--------------------|
| NTR3A30PZT1G | SOT-23 (Pb-Free) | 3000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTR3A30PZ

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|---|-------------------|---|-----|------|----------|----------------------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-to-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$ | -20 | | | V |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | $I_D = -250\ \mu\text{A}$, ref to 25°C | | 10.5 | | mV/ $^\circ\text{C}$ |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{GS} = 0\text{ V}, V_{DS} = -20\text{ V}$ $T_J = 25^\circ\text{C}$ | | | -1 | μA |
| Gate-to-Source Leakage Current | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$ | | | ± 10 | μA |

ON CHARACTERISTICS (Note 3)

| | | | | | | |
|--|------------------|--|------|-------|------|----------------------|
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS} = V_{DS}, I_D = -250\ \mu\text{A}$ | -0.4 | -0.65 | -1.0 | V |
| Negative Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ | | | 10.5 | | mV/ $^\circ\text{C}$ |
| Drain-to-Source On Resistance | $R_{DS(on)}$ | $V_{GS} = -4.5\text{ V}$ $I_D = -3\text{ A}$ | | 31 | 38 | m Ω |
| | | $V_{GS} = -2.5\text{ V}$ $I_D = -2.5\text{ A}$ | | 36 | 50 | |
| | | $V_{GS} = -1.8\text{ V}$ $I_D = -1.5\text{ A}$ | | 51 | 73 | |
| Forward Transconductance | g_{FS} | $V_{DS} = -5\text{ V}, I_D = -3\text{ A}$ | | 30 | | S |

CHARGES AND CAPACITANCES

| | | | | | | |
|------------------------------|--------------|--|--|------|--|----|
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = -15\text{ V}$ | | 1651 | | pF |
| Output Capacitance | C_{oss} | | | 148 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 129 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS} = -4.5\text{ V}, V_{DS} = -15\text{ V}, I_D = -3\text{ A}$ | | 17.6 | | nC |
| Threshold Gate Charge | $Q_{G(TH)}$ | | | 0.7 | | |
| Gate-to-Source Charge | Q_{GS} | | | 2.4 | | |
| Gate-to-Drain Charge | Q_{GD} | | | 4.9 | | |

SWITCHING CHARACTERISTICS (Note 4)

| | | | | | | |
|---------------------|--------------|---|--|------|--|----|
| Turn-On Delay Time | $t_{d(on)}$ | $V_{GS} = -4.5\text{ V}, V_{DS} = -15\text{ V}, I_D = -3\text{ A}, R_G = 6.0\ \Omega$ | | 100 | | ns |
| Rise Time | t_r | | | 208 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 1043 | | |
| Fall Time | t_f | | | 552 | | |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | | |
|-----------------------|----------|--|---------------------------|--|------|-----|---|
| Forward Diode Voltage | V_{SD} | $V_{GS} = 0\text{ V}, I_S = -0.4\text{ A}$ | $T_J = 25^\circ\text{C}$ | | 0.65 | 1.0 | V |
| | | | $T_J = 125^\circ\text{C}$ | | 0.47 | | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width $\leq 300\text{ ms}$, duty cycle $\leq 2\%$.

4. Switching characteristics are independent of operating junction temperatures.

NTR3A30PZ

TYPICAL CHARACTERISTICS

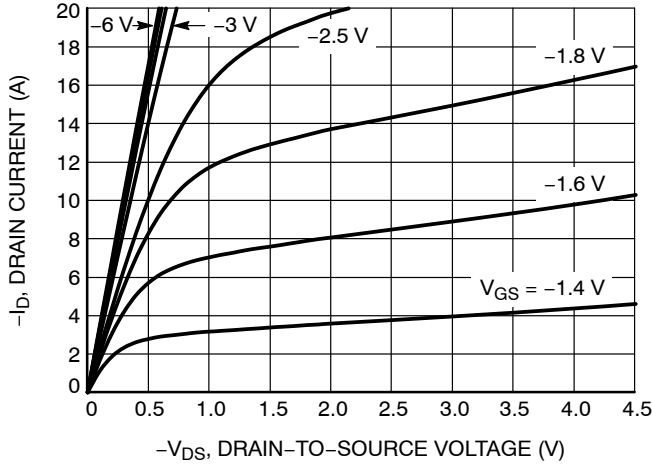


Figure 1. On-Region Characteristics

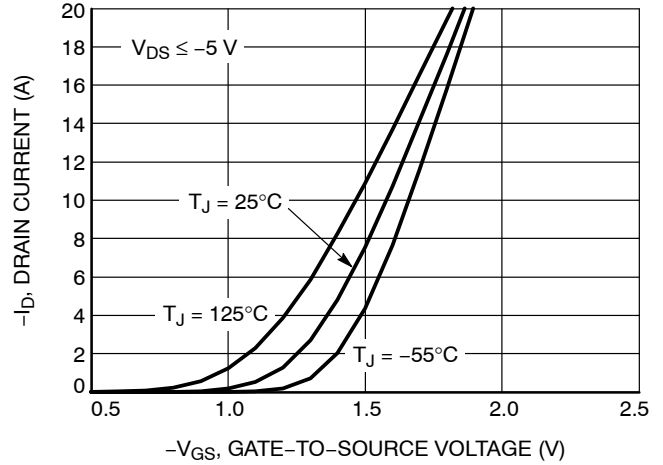


Figure 2. Transfer Characteristics

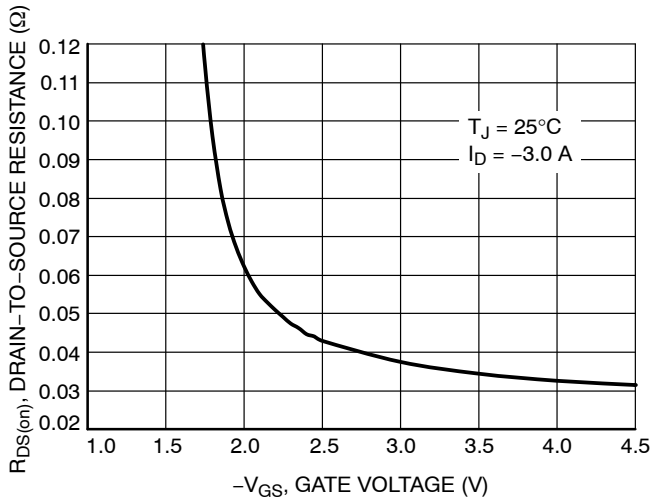


Figure 3. On-Resistance vs. Gate-to-Source Voltage

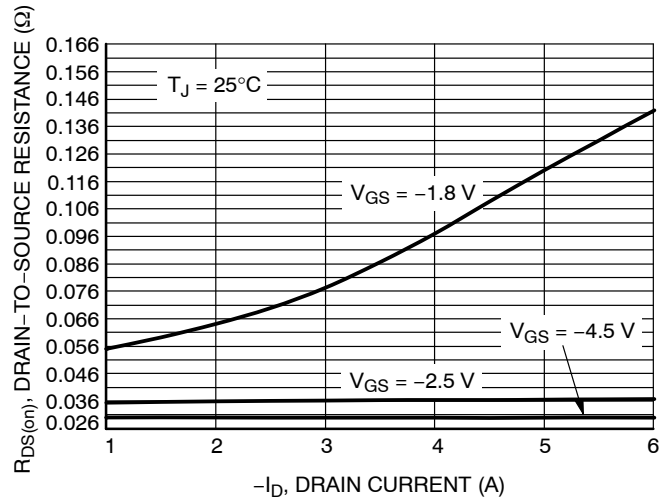


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

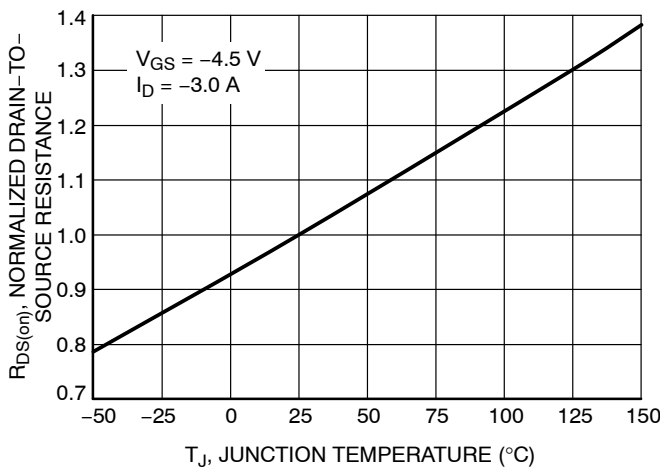


Figure 5. On-Resistance Variation with Temperature

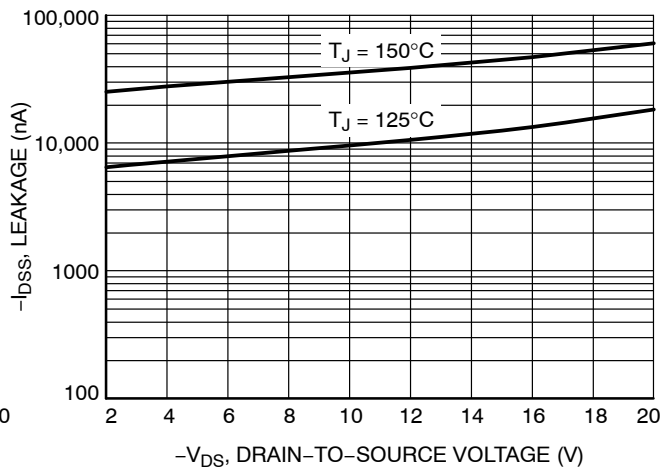


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

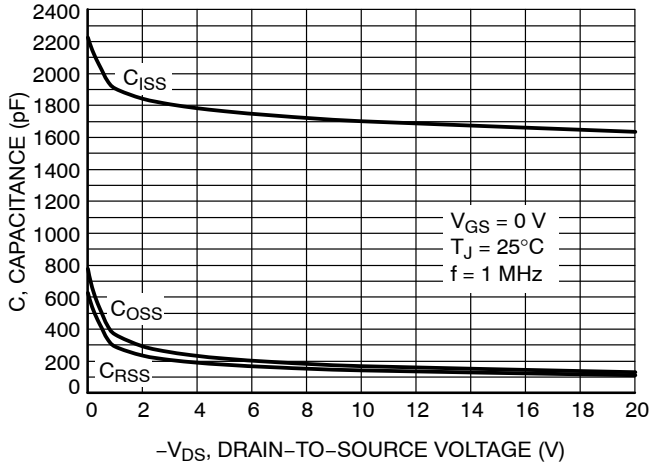


Figure 7. Capacitance Variation

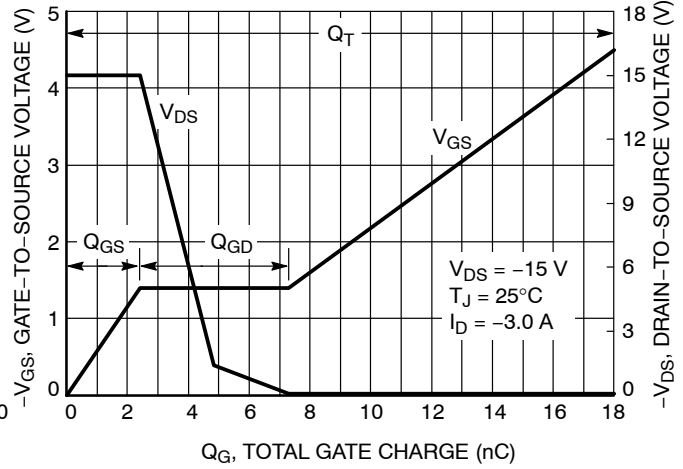


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

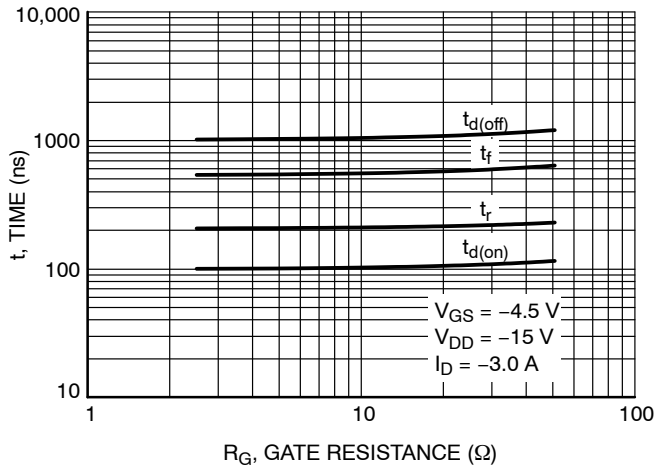


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

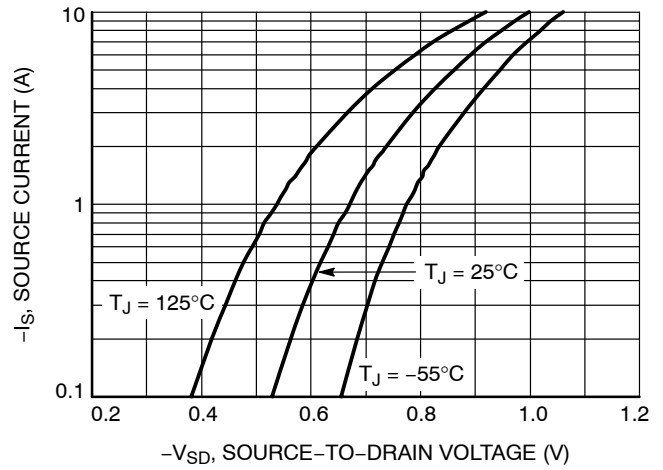


Figure 10. Diode Forward Voltage vs. Current

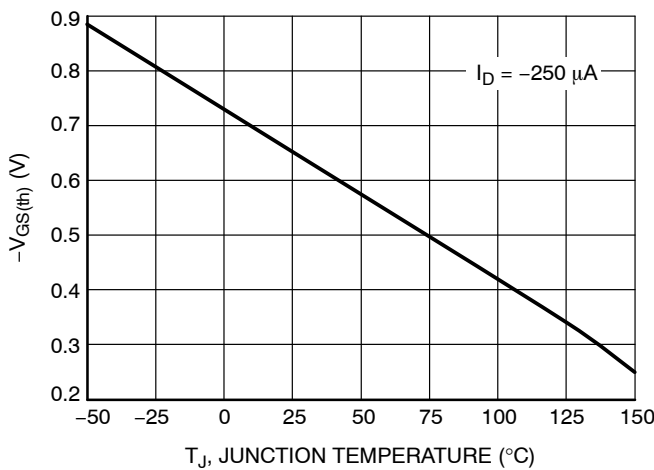


Figure 11. Threshold Voltage

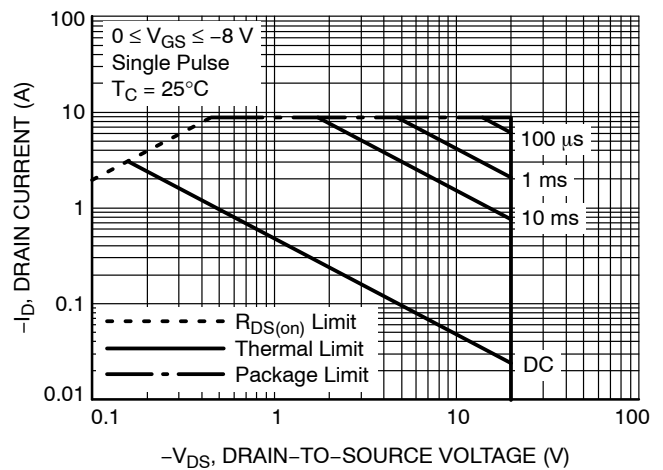


Figure 12. Maximum Rated Forward Biased Safe Operating Area

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TYPICAL CHARACTERISTICS

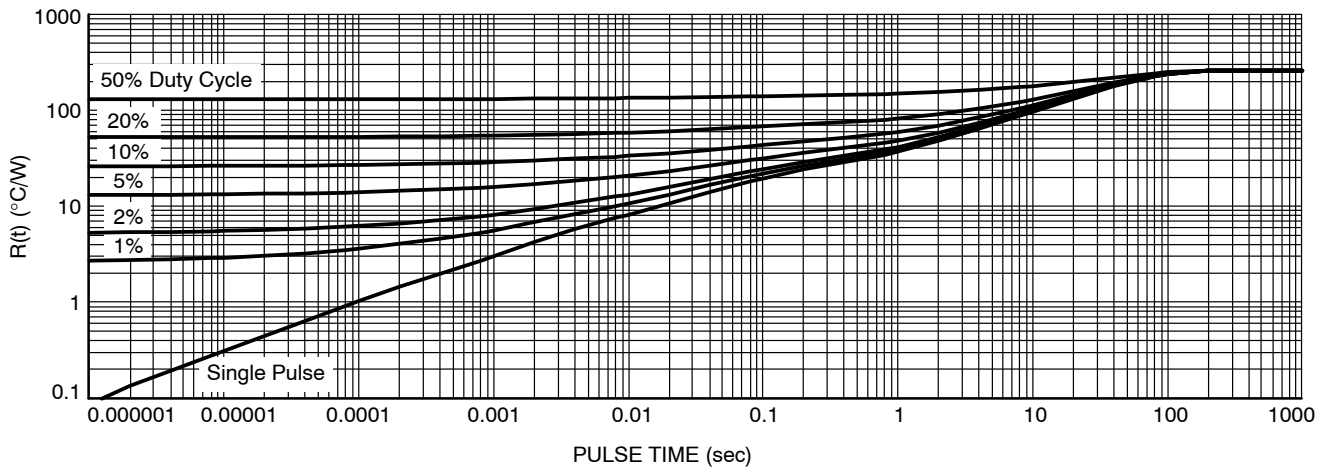


Figure 13. FET Thermal Response

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SOT-23 (TO-236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| DIM | MILLIMETERS | | | INCHES | | |
|----------------|-------------|------|------|--------|-------|-------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | 0.89 | 1.00 | 1.11 | 0.035 | 0.039 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.000 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.017 | 0.020 |
| c | 0.08 | 0.14 | 0.20 | 0.003 | 0.006 | 0.008 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.080 |
| L | 0.30 | 0.43 | 0.55 | 0.012 | 0.017 | 0.022 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.027 |
| H _E | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| T | 0° | --- | 10° | 0° | --- | 10° |

GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



SOT-23 (TO-236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

- | | | | | | |
|---|---|---|---|---|---|
| STYLE 1 THRU 5: CANCELLED | STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR | STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE | | |
| STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE | STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE | STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE | STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE |
| STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE | STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE | STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE | STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE | STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE | STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE |
| STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN | STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT | STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE | STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE | STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION |
| STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE | STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE | | | | |

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